MC74HC173A

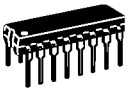
Quad 3-State D Flip-Flop with Common Clock and Reset

High–Performance Silicon–Gate CMOS

The MC74HC173A is identical in pinout to the LS173. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

Data, when enabled, are clocked into the four D flip–flops with the rising edge of the common Clock. When either or both of the Output Enable Controls is high, the outputs are in a high–impedance state. This feature allows the HC173A to be used in bus–oriented systems. The Reset feature is asynchronous and active high.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity 208 FETs or 52 Equivalent Gates



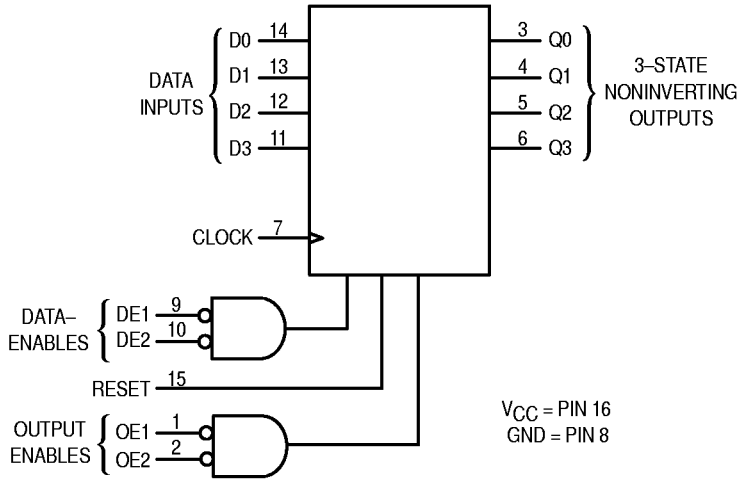
N SUFFIX
16–LEAD PLASTIC DIP PACKAGE
CASE 648–08

D SUFFIX
16–LEAD PLASTIC SOIC PACKAGE
CASE 751B–05

ORDERING INFORMATION

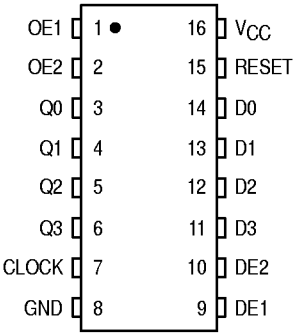
MC74HCXXXAN	Plastic
MC74HCXXXAD	SOIC

LOGIC DIAGRAM



V_{CC} = PIN 16
GND = PIN 8

PIN ASSIGNMENT



FUNCTION TABLE

Inputs							Output
Output Enables				Data Enables		Data	
OE1	OE2	Reset	Clock	DE1	DE2	D	Q
L	L	H	X	X	X	X	L
L	L	L	L	X	X	X	No Change
L	L	L	H	X	X	X	No Change
L	L	L	↑	H	X	X	No Change
L	L	L	↑	X	H	X	No Change
L	L	L	↑	L	L	L	L
L	L	L	↑	L	L	H	H
L	L	L	↓	X	X	X	No Change
L	H	X	X	X	X	X	High Impedance
H	L	X	X	X	X	X	High Impedance
H	H	X	X	X	X	X	High Impedance

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	– 0.5 to V_{CC} + 0.5	V
V_{out}	DC Output Voltage (Referenced to GND)	– 0.5 to V_{CC} + 0.5	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 75	mA
P_D	Power Dissipation in Still Air Plastic DIP†	750	mW
	SOIC Package†	500	
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

* Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the Recommended Operating Conditions.
†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C
SOIC Package: – 7 mW/°C from 65° to 125°C
For high frequency or heavy load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		– 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2.0 V	0	1000	ns
	(Figure 1)	V_{CC} = 4.5 V	0	500	
		V_{CC} = 6.0 V	0	400	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit – 55 to 25°C	Guaranteed Limit ≤ 85°C	Guaranteed Limit ≤ 125°C	Unit
V_{IH}	Minimum High–Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $\|I_{out}\|$ ≤ 20 μA	2.0	1.5	1.5	1.5	V
			3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V_{IL}	Maximum Low–Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $\|I_{out}\|$ ≤ 20 μA	2.0	0.5	0.5	0.5	V
			3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V_{OH}	Minimum High–Level Output Voltage	V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 3.6 mA	3.0	2.48	2.34	2.20	
		$\|I_{out}\|$ ≤ 6.0 mA	4.5	3.98	3.84	3.70	
		$\|I_{out}\|$ ≤ 7.8 mA	6.0	5.48	5.34	5.20	
V_{OL}	Maximum Low–Level Output Voltage	V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 3.6 mA	3.0	0.26	0.33	0.40	
		$\|I_{out}\|$ ≤ 6.0 mA	4.5	0.26	0.33	0.40	
		$\|I_{out}\|$ ≤ 7.8 mA	6.0	0.26	0.33	0.40	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				– 55 to 25°C	≤ 85°C	≤ 125°C	
I_{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum Three–State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	±0.5	±5.0	±10	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND I_{out} = 0 μA	6.0	4	40	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			– 55 to 25°C	≤ 85°C	≤ 125°C	
f_{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 5)	2.0 3.0 4.5 6.0	6.0 10 30 35	4.8 8.0 24 28	4.0 6.0 20 24	MHz
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Clock to Q (Figures 1 and 5)	2.0 3.0 4.5 6.0	175 150 35 30	220 175 44 37	265 220 53 45	ns
t_{PHL}	Maximum Propagation Delay, Reset to Q (Figures 2 and 5)	2.0 3.0 4.5 6.0	150 125 30 26	190 150 38 33	225 175 45 38	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	2.0 3.0 4.5 6.0	150 125 30 26	190 150 38 33	225 175 45 38	ns
t_{PZL}, t_{PZH}	Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	2.0 3.0 4.5 6.0	150 125 30 26	190 150 38 33	225 175 45 38	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 5)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF
C_{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)	—	15	15	15	pF

NOTES:
1. For propagation delays with loads other than 50 pF, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).
2. Information on typical parametric values can be found in Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Flip–Flop)*	35	pF

* Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6$ ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			– 55 to 25°C	≤ 85°C	≤ 125°C	
t_{su}	Minimum Setup Time, Input D or DE to Clock (Figure 4)	2.0 3.0 4.5 6.0	100 75 20 17	125 100 25 21	150 125 30 26	ns
t_h	Minimum Hold Time, Clock to Input D or DE (Figure 4)	2.0 3.0 4.5 6.0	3 3 3 3	3 3 3 3	3 3 3 3	ns
t_{rec}	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0 3.0 4.5 6.0	90 70 18 15	115 95 23 20	135 115 27 23	ns
t_w	Minimum Pulse Width, Clock (Figure 1)	2.0 3.0 4.5 6.0	80 65 16 14	100 90 20 17	120 110 24 20	ns
t_w	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	80 65 16 14	100 90 20 17	120 110 24 20	ns
t_r, t_f	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

PIN DESCRIPTIONS

INPUTS

D0, D1, D2, D3 (Pins 14, 13, 12, 11)

4–bit data inputs. Data on these pins, when enabled by the Data–Enable Controls, are entered into the flip–flops on the rising edge of the clock.

CLOCK (Pin 7)

Clock input.

OUTPUTS

Q0, Q1, Q2, Q3 (Pins 3, 4, 5, 6)

3–state register outputs. During normal operation of the device, the outputs of the D flip–flops appear at these pins. During 3–state operation, these outputs assume a high–impedance state.

CONTROL INPUT

Reset (Pin 15)

Asynchronous reset input. A high level on this pin resets all flip–flops and forces the Q outputs low, if they are not already in high–impedance state.

DE1, DE2 (Pins 9, 10)

Active–low Data Enable Control inputs. When both Data Enable Controls are low, data at the D inputs are loaded into the flip–flops with the rising edge of the Clock input. When either or both of these controls are high, there is no change in the state of the flip–flops, regardless of any changes at the D or Clock inputs.

OE1, OE2 (Pins 1, 2)

Output Enable Control inputs. When either or both of the Output Enable Controls are high, the Q outputs of the device are in the high–impedance state. When both controls are low, the device outputs display the data in the flip–flops.

SWITCHING WAVEFORMS

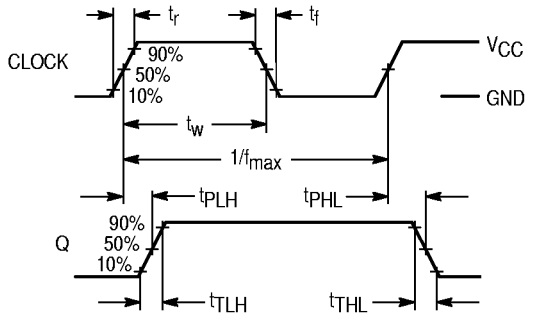


Figure 1.

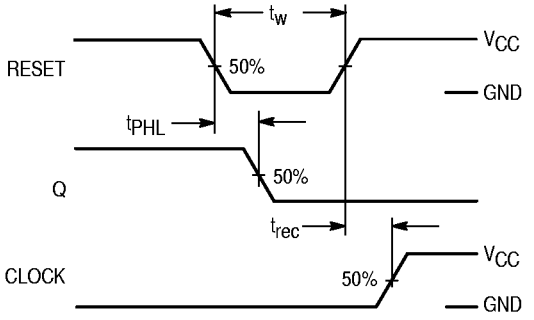


Figure 2.

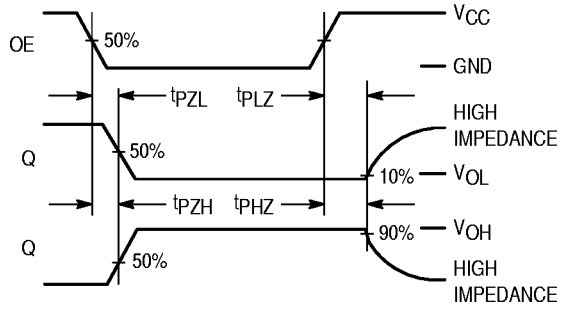


Figure 3.

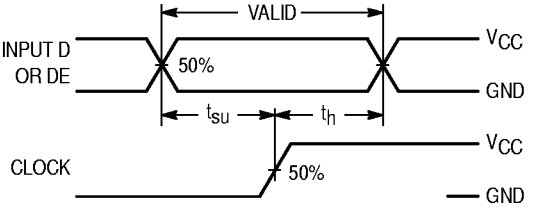
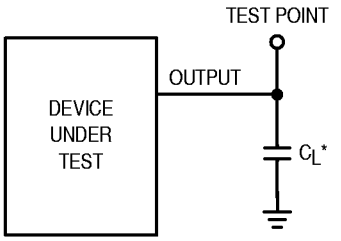


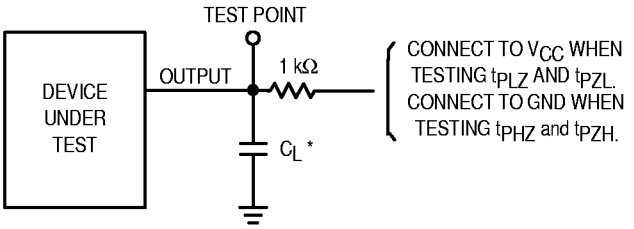
Figure 4.

TEST CIRCUITS



* Includes all probe and jig capacitance

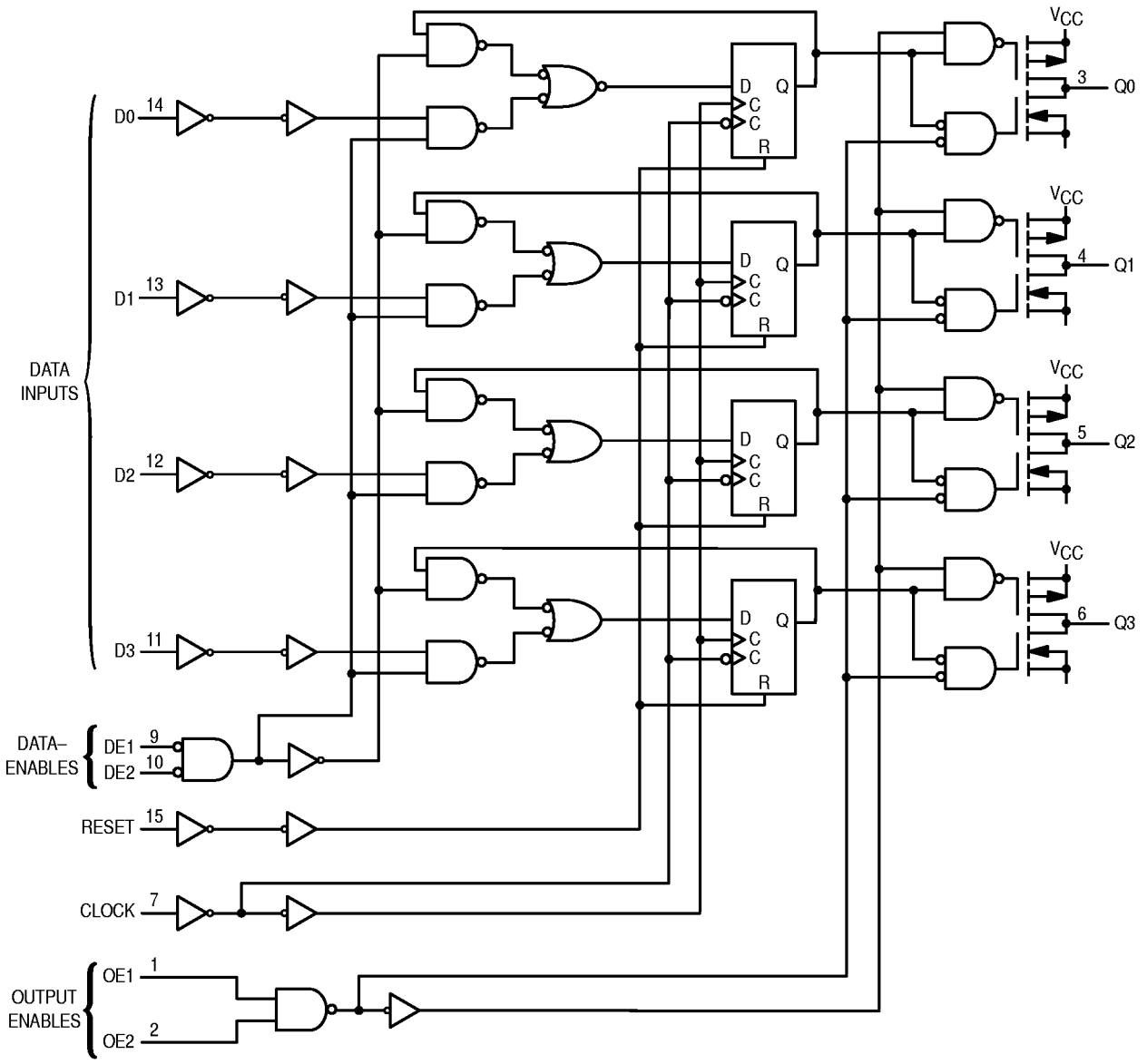
Figure 5.



* Includes all probe and jig capacitance

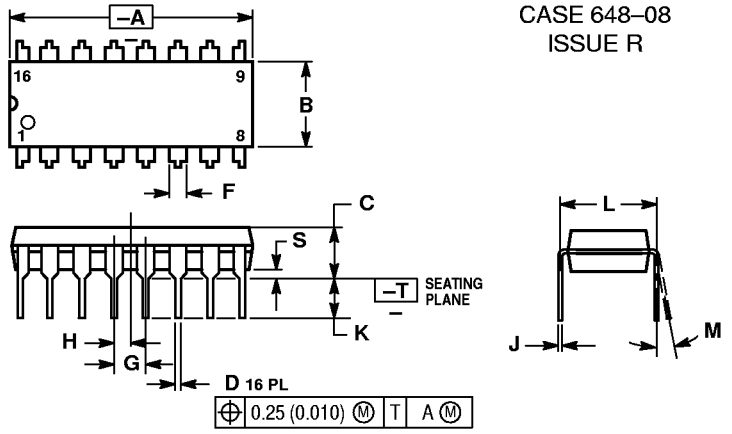
Figure 6.

LOGIC DETAIL



OUTLINE DIMENSIONS

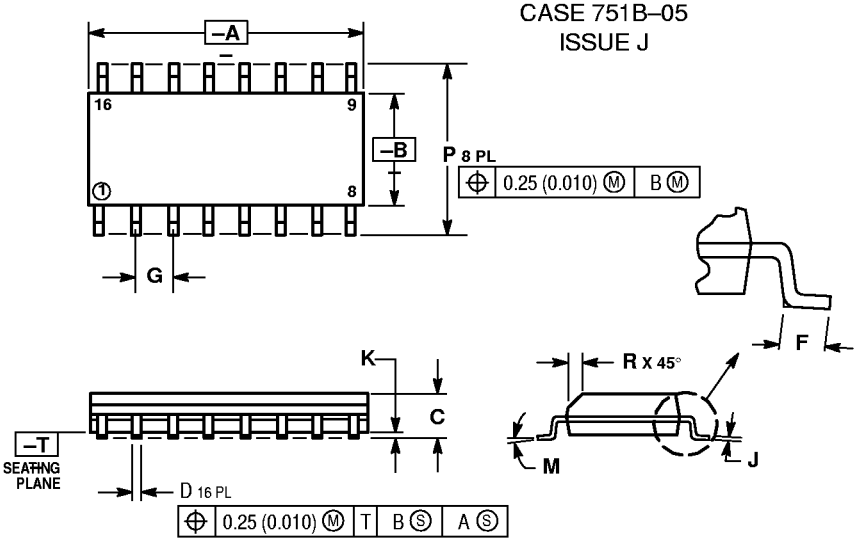
N SUFFIX
PLASTIC PACKAGE
CASE 648–08
ISSUE R



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01

D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751B–05
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

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